

Instrumentation for high energy physics Sergey Barsuk, LAL Orsay, <u>sergey.barsuk@lal.in2p3.fr</u>

- Passage of particles through matter
- Photon detectors
- **Scintillators**
- Cherenkov light detectors, time-of-flight detectors
- **Calorimeters**

Tracking detectors: silicon and gaseous detectors, introduction





Very selective and personal, no way to cover all technologies/detectors Many simplifications, avoid formalism where possible No proper references to the origin for many plots

# TESHEP, Poltava - Ukraine, 13-20/07/2018

Полтавський краєзнавчий музей



### Полтавський краєзнавчий музей



Monday-Sunday 9-17, Wednesday closed

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Gaseous detectors: examples

### My first gaseous detector : Straw Tube

![](_page_4_Figure_1.jpeg)

... and take MANY straws to have high efficiency.

![](_page_4_Figure_3.jpeg)

5

## Straw Tube : LHCb outer tracker

![](_page_5_Picture_1.jpeg)

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Charged track passes through electric field Primary Ek = 10 ... 100 eV (then secondary) ionization  $n_{total} \approx \times 3 \text{ or } \times 4.n_{primary}$ Drift, electrons drift faster Signal multiplication, Gain ~10<sup>4</sup> Signal collection  $\frac{V_{electron}}{V_{ion}} \approx 10^{3}$  in CO<sub>2</sub> with  $E = 10^{4}$  V/cm

# Avalanche development in high E field (~250 kV/cm) around a thin wire (multiplication region ~100 µm):

![](_page_6_Figure_2.jpeg)

#### Gas amplification next to anode wire

![](_page_6_Figure_4.jpeg)

Fast signal induction during avalanche development → sub-ns RESOLUTION !

![](_page_7_Figure_0.jpeg)

Assuming that the total charge of the avalanche Q is produced at a (small) distance  $\lambda$  from the anode, the electron (q<sup>-</sup>) and ion contributions (q<sup>+</sup>) to the total induced signal (q = q<sup>-</sup> +q<sup>+</sup>) on anode are:

![](_page_7_Figure_2.jpeg)

F. Sauli, http://www.cern.ch/GDD

#### **Cloud track picture of a single electron avalanche**

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#### Gas amplification and the saturation effects.

![](_page_8_Figure_1.jpeg)

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![](_page_9_Picture_0.jpeg)

Invented by Georges Charpak in 1968 ... ... Nobel Prise in 1992

### Multi Wire Proportional Chamber (MWPC)

Transformed in high precision Drift Chambers (DC), Time Projection Chamber (TPC) etc.

Applications : X-ray and medical imaging, UV photon detection, neutron, and crystal diffraction and other material science studies, astronomy etc.

![](_page_9_Picture_5.jpeg)

Radiography of Charpak's hand made with a digital X-ray imaging apparatus based on the MWPC

![](_page_10_Figure_0.jpeg)

Figure 28.7: Electric field lines and equipotentials in (a) a multiwire proportional chamber and (b) a drift chamber.

# Figure 28.8: Electric field lines and equipotentials in a multiwire drift module. Each anode wire is surrounded by six cathode wires, and each cathode wire is surrounded by three anode wires.

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# **ARGUS Drift Chamber**

![](_page_11_Picture_1.jpeg)

Hexagonal drift cells formed by potential and sense wires

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#### Time Projection Chamber (TPC)

Large volume active detector.

full 3-D track reconstruction

x-y from wires and segmented cathode (

![](_page_12_Figure_4.jpeg)

... or R-O from both sides :

- Smaller drift distance
- □ Faster signal collection, smaller diffusion

Less requirements to the electric field

Better efficiency

![](_page_12_Figure_10.jpeg)

# ... more difficult for high multiplicities ...

Relativistic Heavy Ion Collider at Brookhaven

High particle multiplicities Low beam intensities

![](_page_13_Figure_3.jpeg)

Image of Au-Au collision in STAR Time Projection Chamber (TPC)

![](_page_14_Picture_0.jpeg)

![](_page_14_Picture_1.jpeg)

![](_page_14_Picture_2.jpeg)

← ALICE TPC field cage

# dE/dx with ALICE TPC

![](_page_15_Figure_1.jpeg)

#### Micro-Pattern Gaseous Detector Technologies

Micro-Strip Gas Chamber (MSGC): thin anode and cathode strips on insulating support

### **MWPC**

![](_page_16_Picture_3.jpeg)

Typical distance between wires limited to 1 mm due to mechanical and electrostatic forces

A. Oed, NIM A263 (1988) 351.

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#### MSGC

![](_page_16_Picture_8.jpeg)

![](_page_16_Figure_9.jpeg)

Typical distance between anodes 200 mum thanks to semiconductor etching technology

But discharges !

![](_page_16_Figure_12.jpeg)

Rate capability limit due to space charge overcome by increased amplifying cell granularity<sub>MSGC Rates</sub>

![](_page_16_Figure_14.jpeg)

### Gas Electron Multiplier (GEM)

- Thin metal-coated polymer foil chemically pierced by a high density of holes
- □ Thickness ~ 50 mum, hole diameter ~ 70 mum, pitch ~140 mum
- □ A difference of potentials between the two GEM electrodes ~ 500V
- Primary electrons released by ionizing particle, drift towards the holes, where high electric field triggers electron multiplication process.

![](_page_17_Figure_5.jpeg)

![](_page_17_Figure_6.jpeg)

![](_page_17_Picture_7.jpeg)

![](_page_17_Picture_8.jpeg)

Electrons collected on patterned readout board
 Fast signal can be detected on lower GEM electrode for trigger or energy discrimination
 All readout electrodes are at ground potential

F. Sauli, NIM A386(1997)531 F. Sauli, http://www.cern.ch/GDD

### Triple Gas Electron Multiplier (GEM)

Full decoupling of amplification stage (GEM) and readout stage (PCB, anode)

![](_page_18_Figure_2.jpeg)

For the same gain the discharge probability in a multi GEM configuration is much smaller.

![](_page_18_Figure_4.jpeg)

Amplification and readout structures can be optimized independently !

![](_page_18_Picture_6.jpeg)

Compass

Totem

NA49-future

![](_page_18_Picture_10.jpeg)

Electron tracks parallel to the cathode plane, passing between cathode and GEM1

![](_page_19_Figure_1.jpeg)

□ Gain with small pitched GEMs at  $\Delta V_{GEM} \approx 346V$  comparable to  $\Delta V_{GEM} \approx 403V$  with standard GEMs.

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### MICROMEsh GAseous chamber (MICROMEGAS)

Parallel plate multiplication in thin gaps between a fine mesh and anode plate

![](_page_20_Figure_2.jpeg)

#### MICROMEsh GAseous chamber (MICROMEGAS)

#### Small gap→ good energy resolution

![](_page_21_Figure_2.jpeg)

![](_page_21_Picture_3.jpeg)

![](_page_21_Picture_4.jpeg)

"Bulk" Micromegas:

![](_page_21_Picture_6.jpeg)

![](_page_21_Picture_7.jpeg)

![](_page_21_Picture_8.jpeg)

![](_page_21_Picture_9.jpeg)

![](_page_21_Picture_10.jpeg)

Poltava, 13-20.07.18

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#### Integrated electronics: pixel readout of MPGD

- □ "InGrid" Concept: By means of advanced wafer processing-technology INTEGRATE MICROMEGAS amplification grid directly (protection layer) on top of CMOS ("Timepix") ASIC
   □ 3D Gaseous Pixel Detector → 2D (pixel dimensions) x 1D (drift time)
- Bump bond pads for Si-pixel
  Detectors Timepix or Medipix2 (256 × 256 pixels of size 55 × 55 µm2) serve as charge collection pads.

![](_page_22_Picture_3.jpeg)

![](_page_22_Picture_4.jpeg)

□ Each pixel can be set to: TOT ≈ integrated charge

TIME = Time between hit and shutter end

![](_page_22_Picture_7.jpeg)

#### "InGrid" Detector: Single Electron Response and Discharges

Observe electrons from an X-ray (5.9 keV) conversion one by one and count them in micro-TPC (6 cm drift)

Provoke discharges by introducing small amount of Thorium in the Ar gas - Thorium decays to Radon 222 which emits 2 alphas of 6.3 & 6.8 MeV

#### $\rightarrow$ Study single electron response

#### → <u>Round-shape images of discharges</u>

![](_page_23_Figure_5.jpeg)

P. Colas, RD51 Collab. Meet., Jun.16-17, 2009, WG2 Meeting M. Fransen, RD51 Collab. Meet., Oct.13-15, 2008, WG2 Meeting

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### Wide choice of gaseous detectors

![](_page_24_Figure_1.jpeg)

Multi Wire Proportional Chambers MWPC Time Projection Chambers Time Expansion Chambers **Proportional Chambers** Thin Gap Chambers Drift Chambers Jet Chambers Straw Tubs Micro Well Chambers Cathode Strip Chambers **Resistive Plate Chambers** Micro Strip Gas Chambers **GEM** - Gas Electron Multiplier Micromegas – Micromesh Gaseous Structure

O. Ullaland

### Silicon detectors (vertices and precise tracking), examples

![](_page_25_Figure_1.jpeg)

## Silicon detectors

![](_page_26_Figure_1.jpeg)

# Doping of semiconductors

<u>n-Type</u> P, As, Sb 5 electrons in the M-shell 1 electron with binding energy 10-50 meV

<u>p-Type</u> B, Al, Ga 3 electrons in the M-shell 1 electron missing

![](_page_27_Figure_3.jpeg)

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![](_page_28_Figure_0.jpeg)

A p-n junction without bias

- Peak electric field at the boundary between the p and the n.

- Clear depletion layer.

D. A. Fraser, The physics of semiconductor devices

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### Apply a reverse bias to extend the depleted region

![](_page_29_Figure_1.jpeg)

**Reversed biased "PIN DIODE"** 

![](_page_29_Figure_3.jpeg)

Electron-hole pairs created By the traversing particle drift in the electric field

 Energy to create e-h pair ~3.6 eV (30 eV for gas detectors)
 MIP gives ~108 e-h pairs /µm

![](_page_30_Figure_0.jpeg)

### Measure coordinate => strips

![](_page_31_Figure_1.jpeg)

# Strips on both sides => 3D measurement

![](_page_31_Figure_3.jpeg)

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# Overlapping strips: DELPHI Vertex Detector

![](_page_32_Figure_1.jpeg)

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#### **VELO: Vertex LOcator**

![](_page_33_Picture_1.jpeg)

![](_page_33_Figure_2.jpeg)

JINST 8 (2013) P08002, arXiv:1405.7808

- 88 semi-circular microstrip Si sensors
- Double-sided, R and φ layout, in each module
- $\Box$  300 $\mu$  thick n-on-n sensors
- $\Box$  Strip pitches from 40 to  $120\mu$

![](_page_33_Picture_8.jpeg)

![](_page_33_Picture_9.jpeg)

 First active strip at 8.2mm from the beam axis
 Moves away every fill and centers around the beam with self measured vertices

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VELO: precise reconstruction of tracks and vertices

- □ Excellent spatial resolution, down to 4µ for single tracks
- Precise impact parameter measurement,

 $\sigma_{\rm IP} = 11.6 + 23.4/pT \ [\mu]$ 

□ Precise primary vertex reconstruction,  $\sigma_x = \sigma_x = 13\mu$ ,  $\sigma_z = 69\mu$  for a vertex of 25 tracks

Detector well understood, simulation describes data
 VELO provides excellent proper time resolution

![](_page_34_Figure_6.jpeg)

![](_page_34_Figure_7.jpeg)

![](_page_34_Figure_8.jpeg)

## Resolution is the spread of the reconstructed position minus the true position For one strip clusters "top hat" residuals

![](_page_35_Figure_1.jpeg)

□ In practice, resolution degraded by many factors: relation between pitch and diffusion (typically 25-150 mum and 5-10 mum), statistical fluctuations of energy deposit, ...

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#### Si-detector module

![](_page_36_Picture_1.jpeg)

#### Front-end electronics and connectivity: wire bonding

Wire bonding – A "mature" technology (has been around for 40 years) → conventional technique for connecting sensors to each other and to the front-end chips.

![](_page_37_Picture_2.jpeg)

![](_page_37_Picture_3.jpeg)

• Uses ultrasonic power to vibrate needle-like tool on top of wire (17-25 um Al wire). Friction welds wire to metalized substrate underneath.

• Heavily used in industry (PC processors) but not with such thin wire or small pitch.

![](_page_38_Figure_0.jpeg)

Poltava, 13-20.07.18

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### Advanced concepts: 3D Silicon Sensors

□ Challenges for tracking at the future LHC upgrade (sLHC) → current planar-Si sensors technology is not radiation hard to survive to the end of sLHC in the inner layers (R ~ 4 cm)

![](_page_39_Figure_2.jpeg)

Very small depletion & drift distances:

hole diameter: 10  $\mu m$  distance  ${\sim}20{\text{-}}50~\mu m$ 

C. Da Via et al, Nucl. Instr. and Meth. A509(2003)86

![](_page_39_Figure_6.jpeg)

- Maximum drift and depletion distance governed by electrode spacing:
- □ Lower depletion voltages
- □ Faster/more efficient charge collection
- □ Small leakage currents
- Higher radiation hardness
- Narrow dead regions at the edges

 $\rightarrow$  At the price of more complex processing

**Instrumentation - 4** 

With that we are at **the end** of (fast) lecture series on instrumentation.

### You are supposed to retain from these lectures :

- Instrumentation by itself is a fascinating area
- However, instrumentation is a tool, it should be considered only in view of a given physics task
- $\hfill\square$  Conceptual comprehension of the instrumentation is essential even for a theorist  $\hfill\bigcirc$
- □ There is a big variety of techniques for each method ... the choice is often modulated by optimization of performance-background\_conditions-reliability-...-cost
- □ Complex detector is often designed for many physics tasks, detector choice is sometimes a compromise between their requirements
  - $\rightarrow$  requires cross-detector optimization
    - e.g. : tracking precision vs. material in front of calorimeter

 $\rightarrow\,$  requires often detailed simulation, and always understanding/experience of physics analysis and instrumentation techniques

→ requires often simultaneous optimization of the whole chain : detector - front-end electronics - trigger/readout

Despite increasing complexity of detector systems, you can still have a pleasure working on it, and there is still much room for your new bright ideas

Propose an experiment to search for the process  $D^{\circ} \rightarrow e^{+}e^{-}$ 

Q

![](_page_41_Figure_1.jpeg)

□ Very rare decay, FCNC

 $\Box$  In SM: BR up to 10<sup>-13</sup>

 $\Box$  R-parity violation: BR up to 10<sup>-12</sup>

□ Experiment: BR < 7.9 x 10<sup>-8</sup> @ 90% CL